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## TSMBJ0306C THRU TSMBJ0324C

### Features

- Oxide-Glass passivated Junction
- Bi-Directional protection in a single device
- Surge capabilities up to 50A@10/1000us or 150A@8/20us
- High Off-State impedance and Low On-State voltage
- Plastic material has UL flammability classification 94V-0

### Transient Voltage Protection Device 75 to 320 Volts

### Mechanical Data

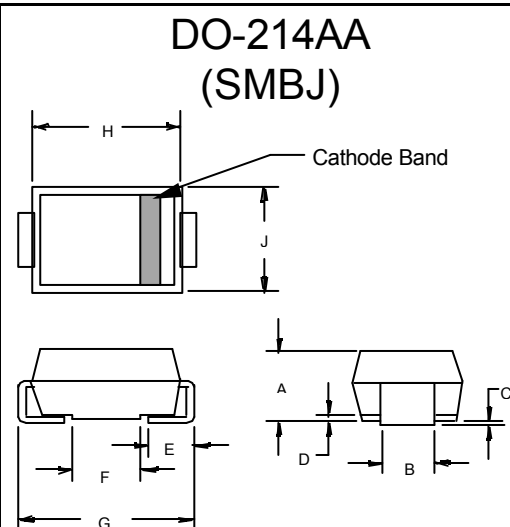
- Case : Molded plastic
- Polarity : None cathode band denotes
- Approx Weight : 0.093grams

### Maximum Rating

Characteristic	Symbol	Value	Unit
Non-repetitive peak impulse current	$I_{PP}$	50A	10/1000us
Non-repetitive peak On-state current	$I_{TSM}$	20A	8.3ms, one-half cycle
Operating temperature range	$T_{OP}$	-40~125°C	
Junction and storage temperature range	$T_J, T_{STG}$	-55~150°C	

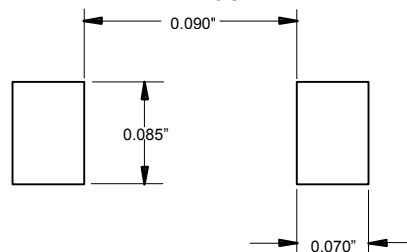
### Thermal Resistance

Characteristic	Symbol	Value	Unit
Thermal Resistance junction to lead	$R_{\theta JL}$	30°C/W	
Thermal Resistance junction to ambient	$R_{\theta JA}$	120°C/W	On recommended pad layout
Typical positive temperature coefficient for breakdown voltage	$\Delta V_{BR}/\Delta T_J$	0.1%/°C	



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.078	.096	2.00	2.44	
B	.077	.083	1.96	2.10	
C	.002	.008	.05	.20	
D	—	.02	—	.51	
E	.030	.060	.76	1.52	
F	.065	.091	1.65	2.32	
G	.205	.220	5.21	5.59	
H	.160	.180	4.06	4.57	
J	.130	.155	3.30	3.94	

#### SUGGESTED SOLDER PAD LAYOUT



# TSMBJ0306C thru TSMBJ0324C

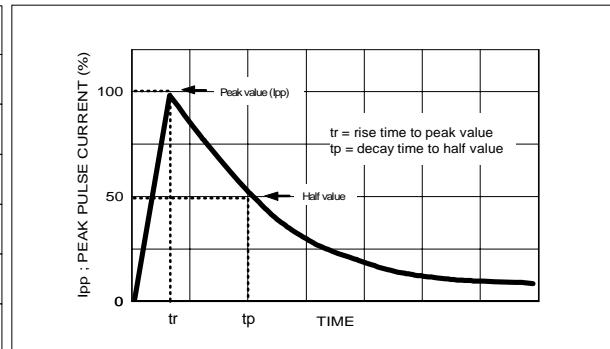


## ELECTRICAL CHARACTERISTIC @25°C Unless otherwise specified

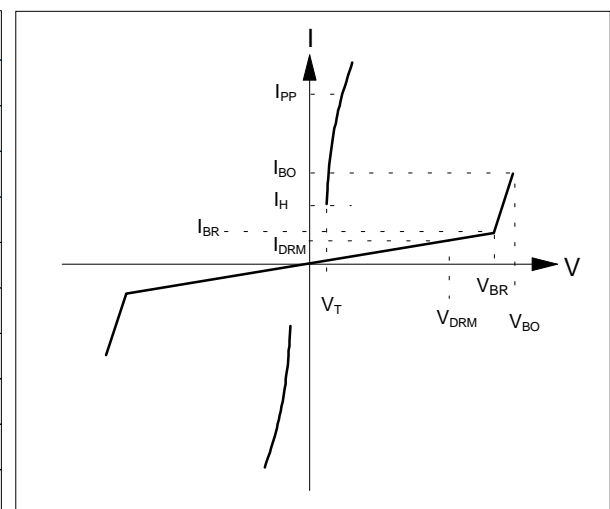
Parameter	Rated Repetitive Off-state Voltage	Off-state Leakage Current@V <sub>DRM</sub>	Breakover Voltage	On-State Voltage @I <sub>T</sub> =1.0A	Breakover Current		Holding Current		Off-State Capacitance
					I <sub>BO</sub>	I <sub>BO+</sub>	I <sub>H</sub>	I <sub>H+</sub>	
Symbol	V <sub>DRM</sub>	I <sub>DRM</sub>	V <sub>BO</sub>	V <sub>T</sub>	I <sub>BO</sub>	I <sub>BO+</sub>	I <sub>H</sub>	I <sub>H+</sub>	C <sub>J</sub>
Units	Volts	uA	Volts	Volts	mA	mA	mA	mA	pF
Limit	Max	Max	Max	Max	Min	Max	Min	Max	Typ.
TSMBJ0306C	75	5	98	5	50	800	150	800	100
TSMBJ0307C	90	5	130	5	50	800	150	800	60
TSMBJ0310C	140	5	180	5	50	800	150	800	60
TSMBJ0312C	160	5	220	5	50	800	150	800	60
TSMBJ0316C	190	5	265	5	50	800	150	800	40
TSMBJ0318C	220	5	300	5	50	800	150	800	40
TSMBJ0322C	275	5	350	5	50	800	150	800	40
TSMBJ0324C	320	5	400	5	50	800	150	800	40

### MAXIMUM RATED SURGE WAVEFORM

Waveform	Standard	I <sub>pp</sub> (A)
2/10 us	GR-1089-CORE	200
8/20 us	IEC 61000-4-5	150
10/160 us	FCC Part 68	100
10/700 us	ITU-T K20/21	60
10/560 us	FCC Part 68	60
10/1000 us	GR-1089-CORE	50



Symbol	Parameter	
V <sub>DRM</sub>	Stand-off voltage	
I <sub>DRM</sub>	Leakage current at stand-off voltage	
V <sub>BR</sub>	Breakdown voltage	
I <sub>BR</sub>	Breakdown current	
V <sub>BO</sub>	Breakover voltage	
I <sub>BO</sub>	Breakover current	
I <sub>H</sub>	Holding current	NOTE: 1
V <sub>T</sub>	On state voltage	
I <sub>PP</sub>	Peak pulse current	
C <sub>O</sub>	Off-state capacitance	NOTE: 2



#### NOTE :

1.  $I_H > (V_L / R_L)$  If this criterion is not obeyed, the TSPD triggers but does not return correctly to high-resistance state. The surge recovery time. It does not exceed 30ms.
2. Off-state capacitance measured at f=1.0MHz, 1.0Vrms signal, VR=2Vdc bias.

# TSMBJ0306C thru TSMBJ0324C



Fig.1 - Off-State Current v.s Junction Temperature

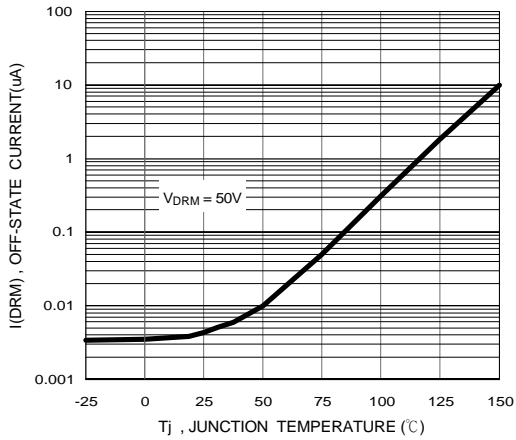


Fig.2 - Relative Variation of Breakdown Voltage v.s Junction Temperature

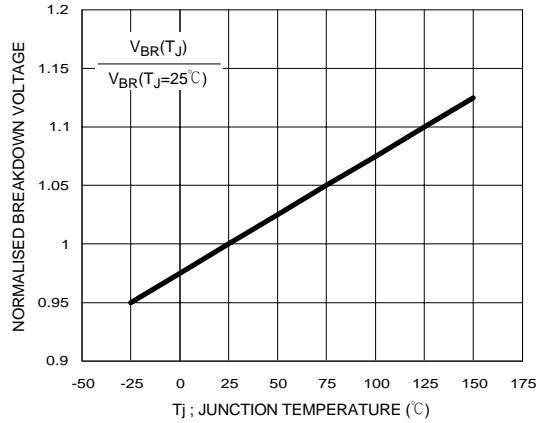


Fig.3 - Relative Variation of Breakover Voltage v.s Junction Temperature

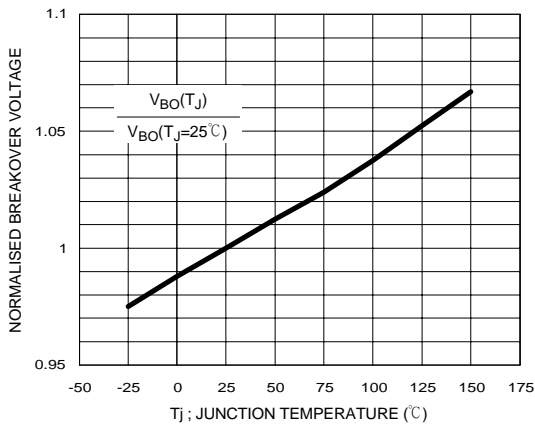


Fig.4 - On-State Current v.s On-State Voltage

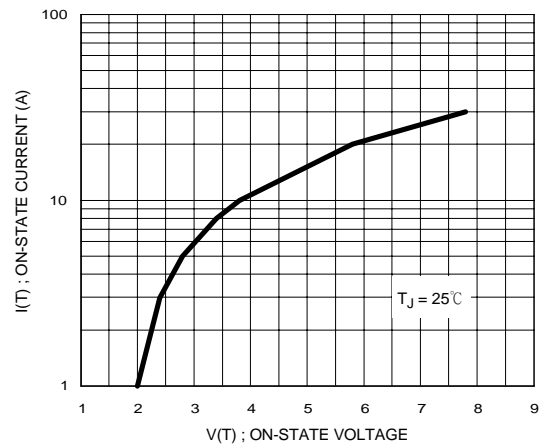


Fig.5 - Relative Variation of Holding Current v.s Junction Temperature

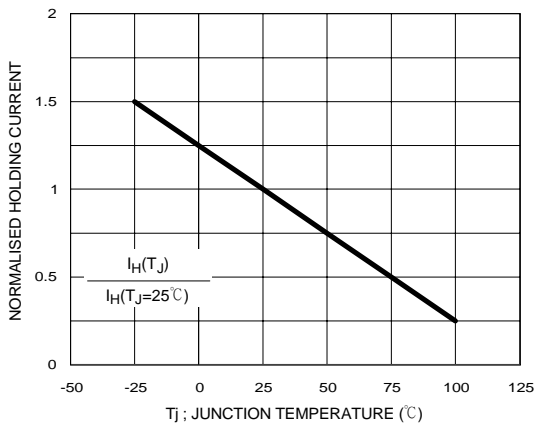
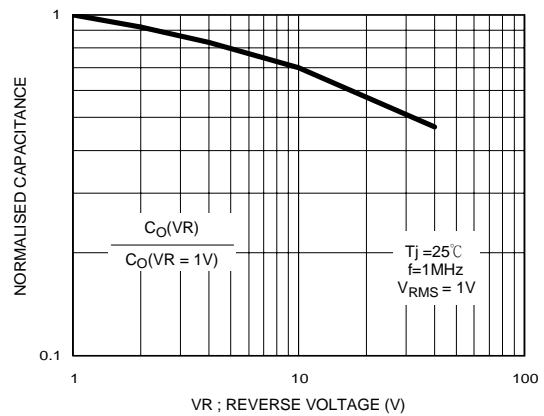
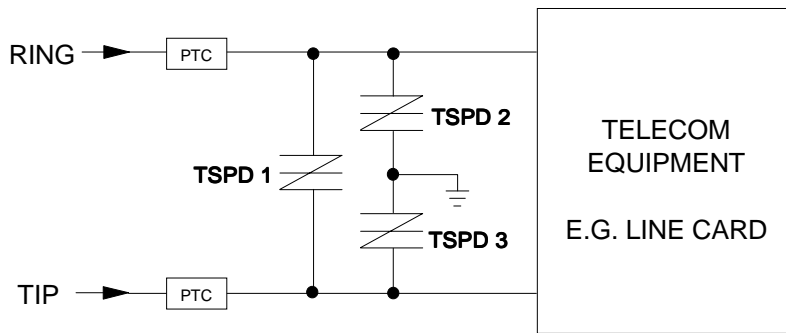
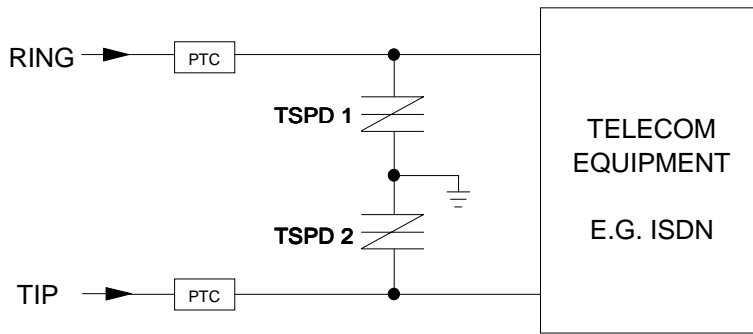
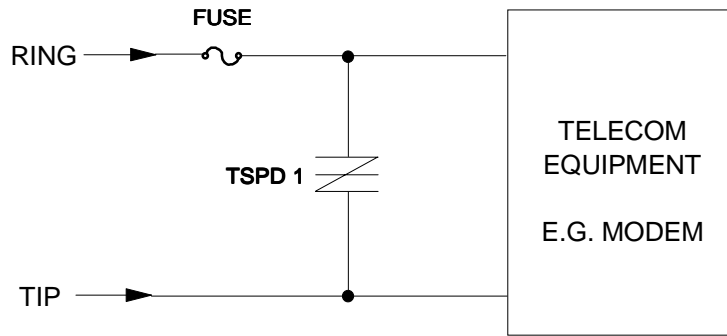


Fig.6 - Relative Variation of Junction Capacitance v.s Reverse Voltage Bias



TYPICAL APPLICATION CIRCUITS



The PTC (Positive Temperature Coefficient) is an overcurrent protection device.